
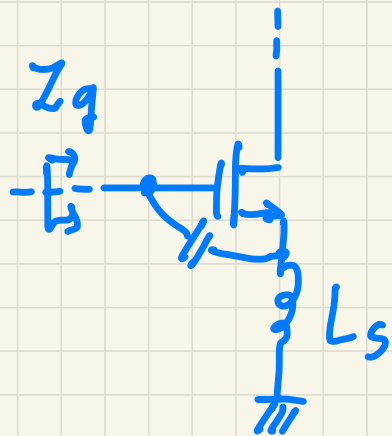


RF Circuit Design

L19

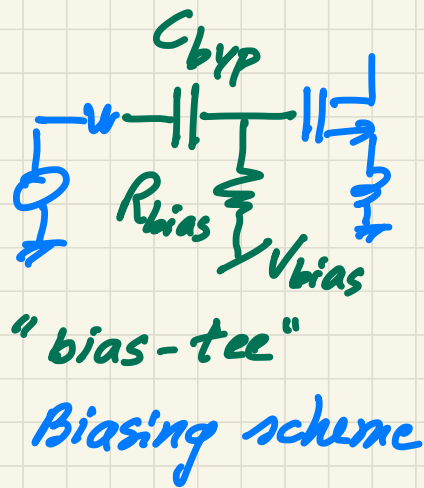
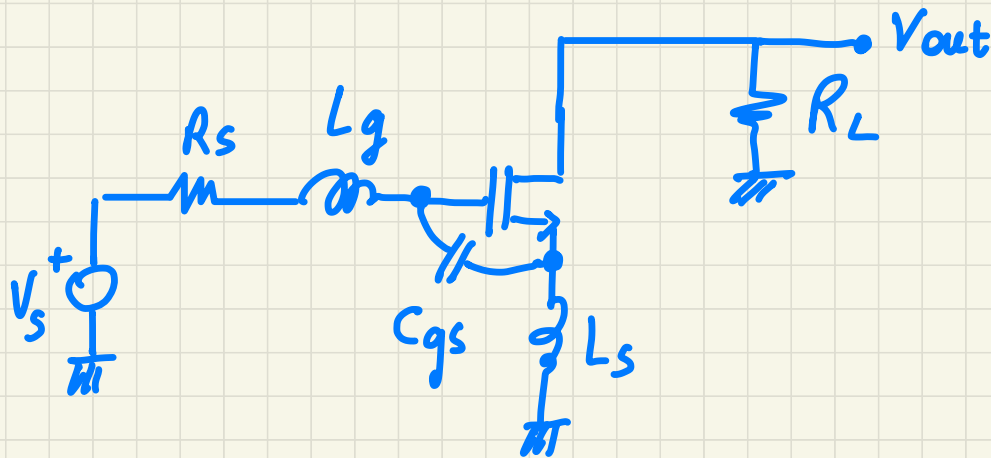


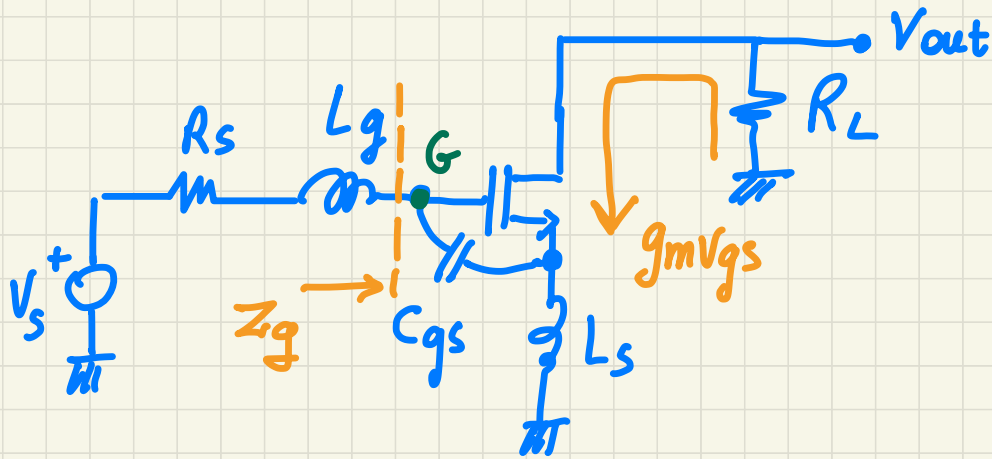
Inductive degeneration



$$Z_g =$$

$$Z_g = \underbrace{\frac{1}{sC_{gs}} + sL_s}_{\text{resonator}} + \underbrace{\omega_r L_s}_{\text{equivalent resistance}}$$





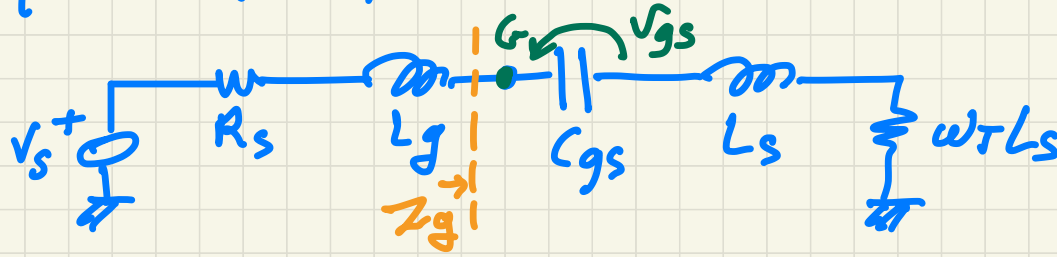
$$\omega_T = \frac{g_m}{C_{gs}}$$

Matching condition :

- $\omega_T L_s = R_s$

- $\omega_0 = \frac{1}{\sqrt{(L_g + L_s) C_{gs}}}$

Equivalent input network



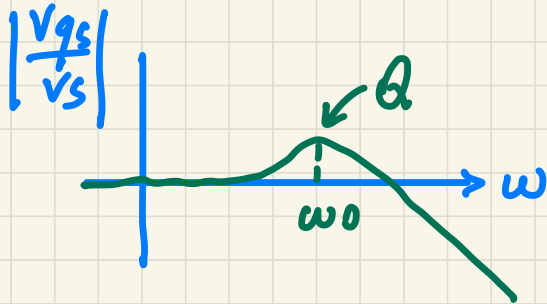
$$\Rightarrow V_{gs} = Q \cdot V_s$$

- Amplifier voltage gain :

$$V_{out} = -g_m R_L V_{gs} = -g_m R_L \cdot Q \cdot V_s$$

$$\text{at } \omega_0 = \frac{1}{\sqrt{(L_s + L_g)C_{gs}}}$$

$$Q = \frac{1}{\omega_0 C_{gs} (R_s + \omega_T L_s)} \quad \xrightarrow{\text{matched}} \quad \frac{1}{\omega_0 C_{gs} \cdot 2R_s}$$



matched

⇓

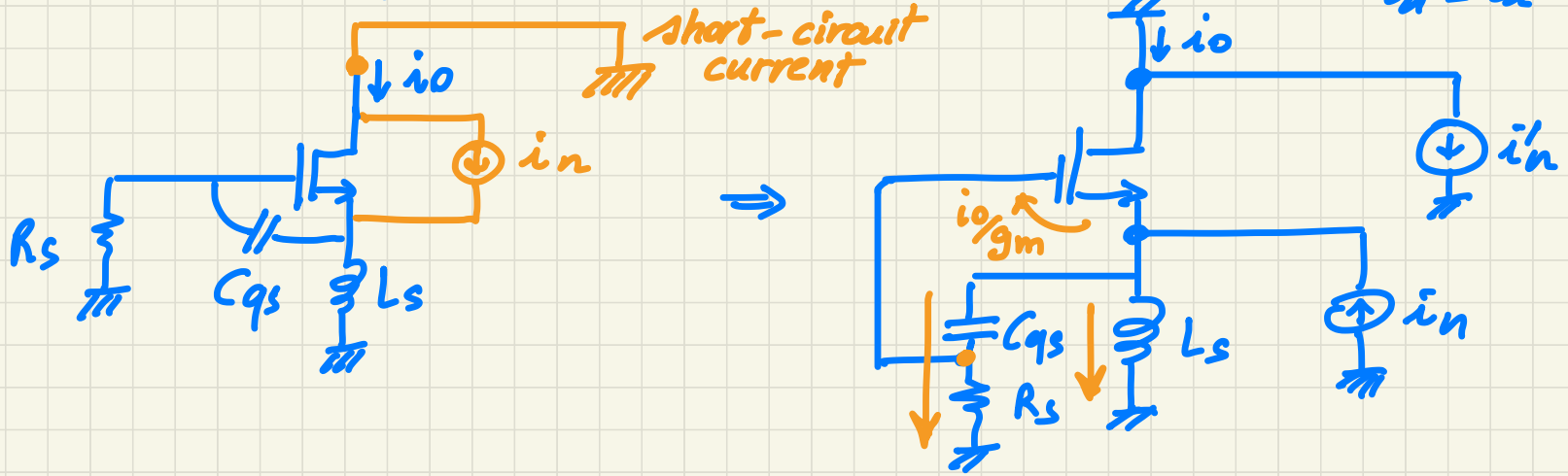
$$A_0 = \frac{V_{out}}{V_s} = -g_m R_L \cdot Q$$

gain of CS topology

gain of impedance transform. network

$$\Rightarrow A_0 = -\underbrace{g_m R_L}_{\text{matched}} \cdot \frac{1}{\omega_0 C_{gs} \cdot 2R_s} = -\underbrace{\frac{\omega_T}{\omega_0}}_{\text{increasing factor}} \cdot \underbrace{\frac{R_L}{2R_s}}_{\text{gain of CG topology}}$$

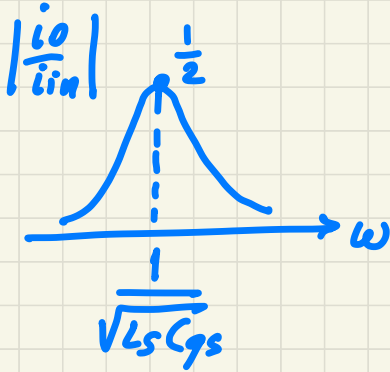
• Noise figure : MOSFET noise



$$i_n + i_o = - \underbrace{\frac{i_o}{g_m} \cdot s C_{gs}}_{\text{current in } C_{gs}} + \underbrace{\frac{-\frac{i_o}{g_m} \cdot s C_{gs} \cdot R_s - \frac{i_o}{g_m}}{s L_s}}_{\text{current in } L_s} ;$$

$$i_o \left(1 + \frac{s C_{gs}}{g_m} + \frac{R_s C_{gs}}{g_m L_s} + \frac{1}{s g_m L_s} \right) = - i_n$$

$$\bullet \frac{i_o}{i_{in}} = - \frac{1 \cdot g_m / C_{gs}}{s^2 + s \left(\frac{g_m}{C_{gs}} + \frac{R_s}{L_s} \right) + \frac{1}{L_s C_{gs}}}$$

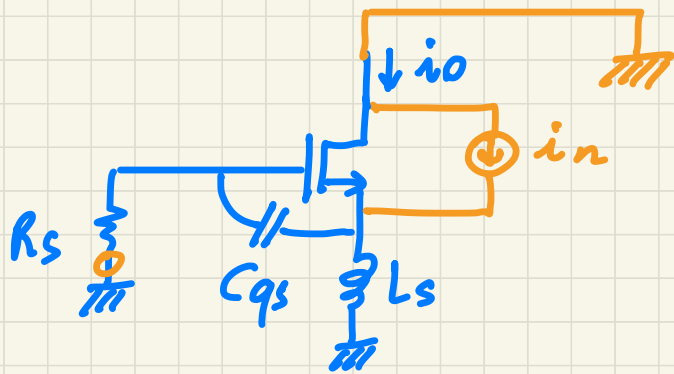


$$\left. \frac{i_o}{i_{in}} \right|_{\text{at resonance}} = - \frac{\cancel{j\omega_0} g_m / C_{gs}}{\cancel{j\omega_0} \left(\frac{g_m}{C_{gs}} + \frac{R_s}{L_s} \right)} =$$

$$= - \frac{\omega_r L_s}{\omega_r L_s + R_s} \quad \uparrow \quad = - \frac{1}{2}$$

input matching

$$\bullet \frac{i_o}{i_{in'}} = 1 \quad \Rightarrow \quad \text{superposition : } \left. \frac{i_o}{i_{in}} \right|_{\text{at res.}} = -\frac{1}{2} + 1 = \frac{1}{2}$$



$$\frac{\cancel{4kT} \frac{\gamma}{\alpha} \cancel{g_m} \cdot \frac{1}{4} \overbrace{\left| \frac{i_o}{i_{in}} \right|^2}^{\text{NF component}}}{\cancel{4kTR_s} \cdot \frac{g_m^2}{\omega_0^2 C_{gs}^2 \cdot \cancel{4R_s^2}}} =$$

$$= \frac{\gamma}{\alpha} \cdot \frac{R_s \omega_0^2 C_{gs}^2}{g_m}$$

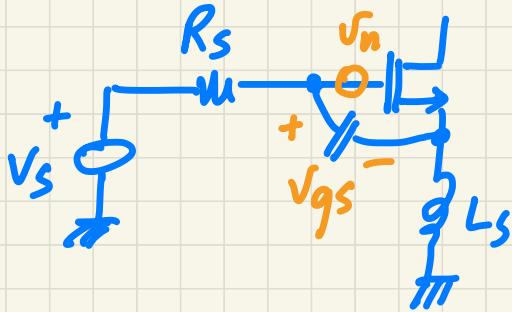
$$= \frac{\gamma}{\alpha} \cdot \frac{\omega_0}{\omega_T} \cdot \underbrace{\omega_0 C_{gs} R_s}_{1/Q_L} =$$

$$= \frac{\gamma}{\alpha} \cdot \frac{\omega_0}{\omega_T} \cdot \frac{1}{Q_L}$$

\uparrow
quality factor of Z_g netw.
(in matching conditions)

$$\Rightarrow NF = 1 + \underbrace{\frac{\gamma}{\alpha}}_{\text{term in CG or shunt-feedb. topologies}} \cdot \underbrace{\frac{\omega_0}{\omega_T} \cdot \frac{1}{Q_L}}_{\text{reduction factor}} + \underbrace{\frac{4 R_S}{R_L}}_{\text{term in CG top.}} \cdot \underbrace{\left(\frac{\omega_0}{\omega_T}\right)^2}_{\text{reduct. factor}}$$

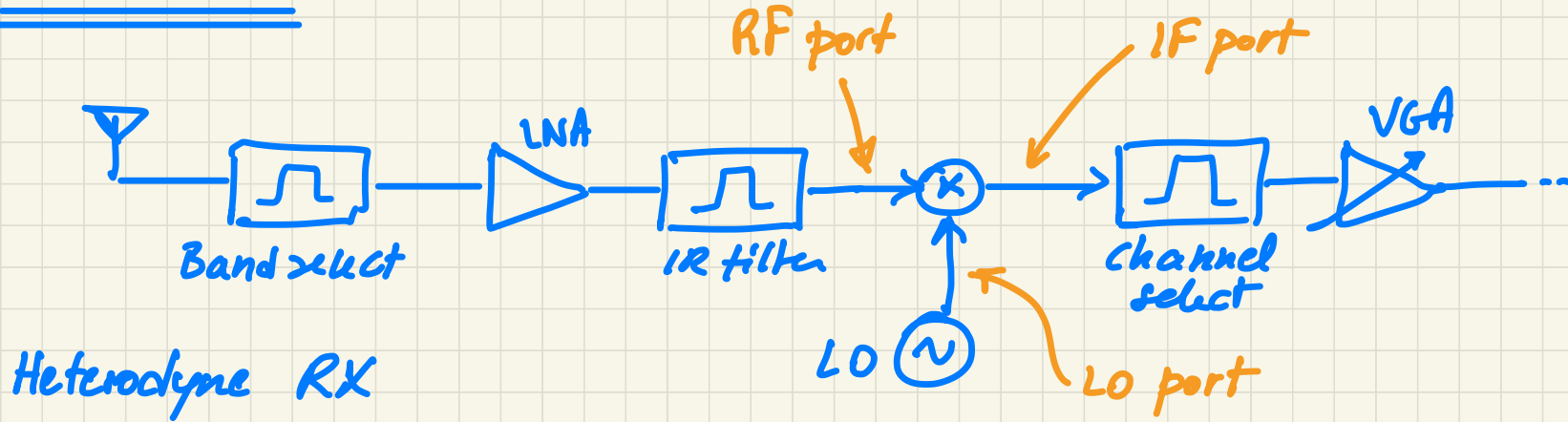
MOS noise
 R_L noise



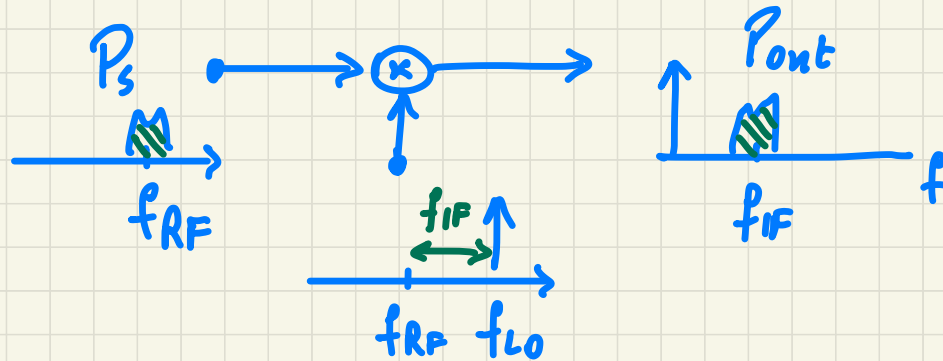
$Q_L \uparrow$ $Q \uparrow$
 larger v_{gs} signal compared
 to v_n (equivalent MOSFET
 noise)

→ narrowband input matching

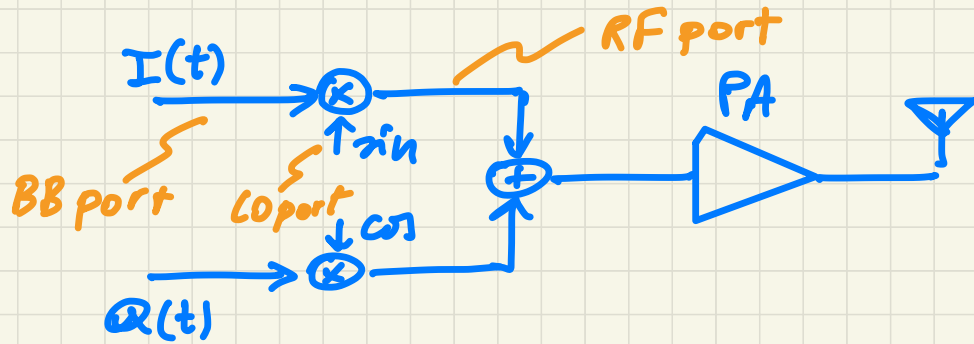
Mixers



Mixer is used as a DOWN-converter



Direct-conversion TX



Mixer is used as an up-converter

Specifications :

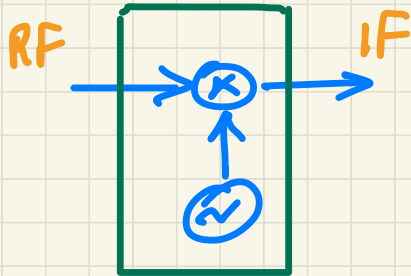
- Conversion gain :

$$G \triangleq \frac{P_{out}}{P_s}$$

power at f_{IF} (pointing to P_{out})

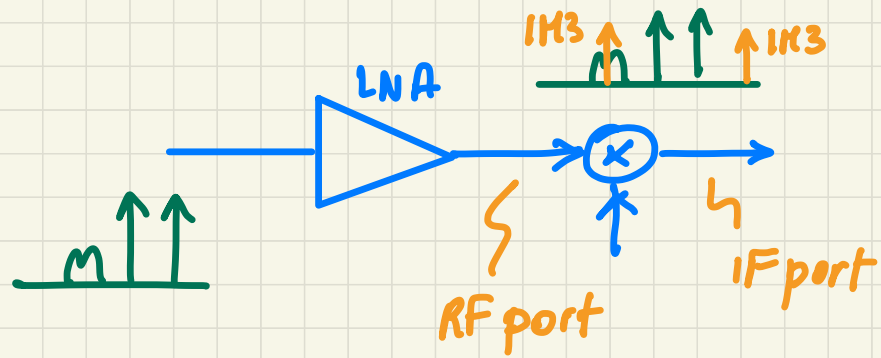
power at f_{RF} (pointing to P_s)

case of DOWN convers.



1/3 mixer

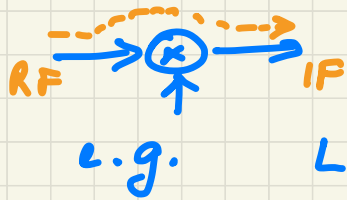
- Linearity : signal at RF port is linearly transferred to IF port



Both IP_3 of LNA
and IP_3 of mixer
matter

- Noise : NF_{mixer} LNA gain is limited (case RX)

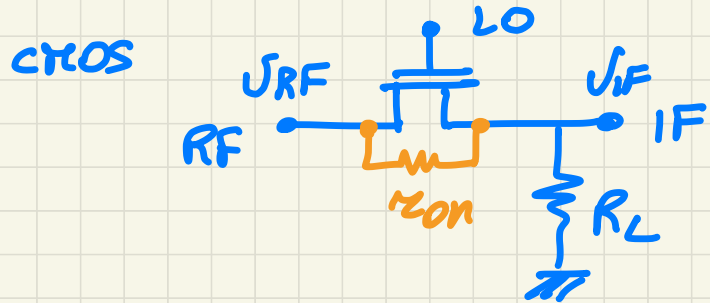
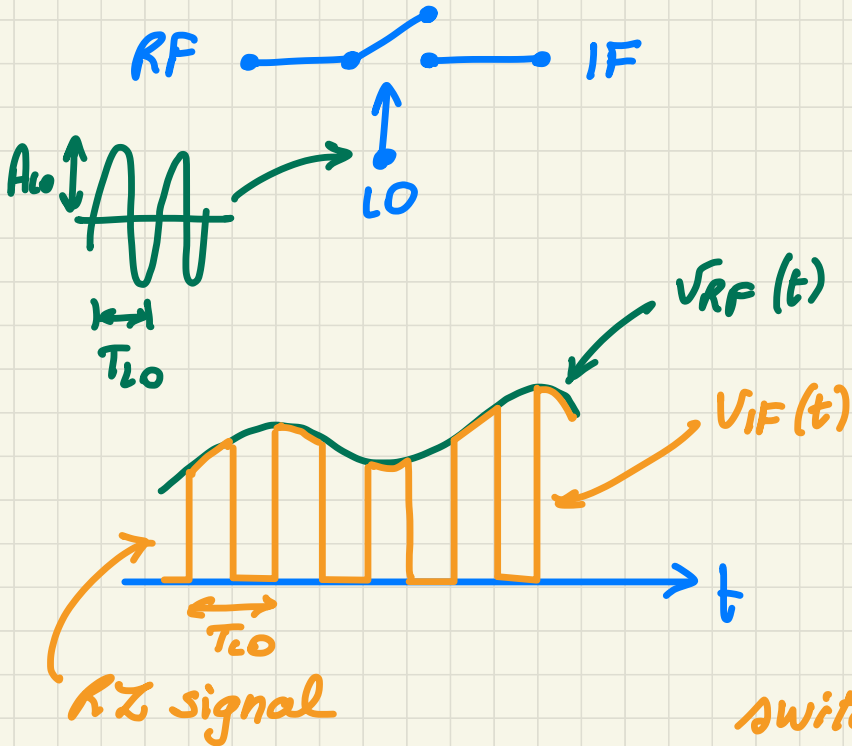
- Feedthroughs : unwanted signal transfers from one to another port



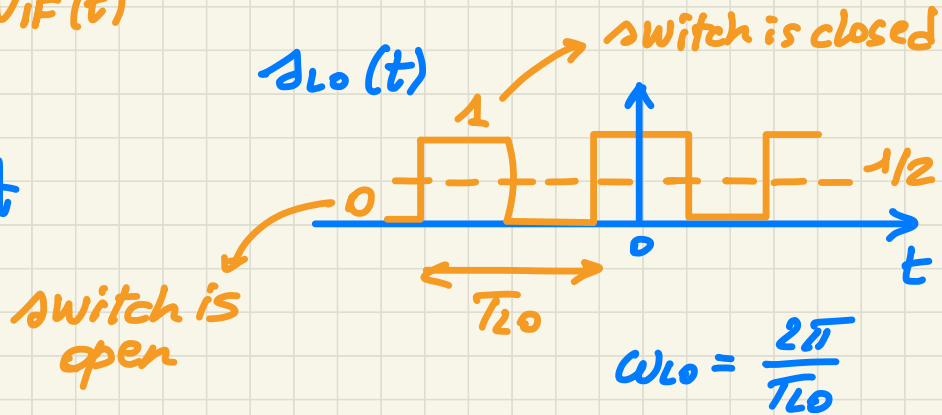
LO - to - RF
LO - to - IF
RF - to - IF

signal at RF input leaks into
IF output : at IF port
there is a signal component
at f_{RF} (case RX)

Passive Return-to-zero (RZ) mixer

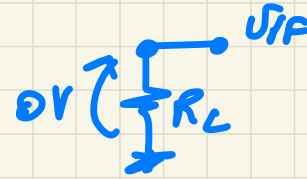
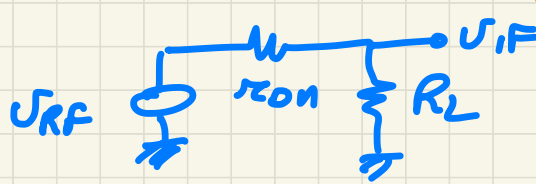


Define a function:



$$\Rightarrow V_{IF}(t) \approx \frac{R_L}{R_L + r_{on}} \cdot s_{LO}(t) \cdot V_{RF}(t)$$

constant r_{on}
(independent on
MOSFET biasing
over time)



\Rightarrow LTV system (ideally if r_{on} is constant)

$$V_{IF}(t) \approx \frac{R_L}{R_L + r_{on}} \cdot \left[\underbrace{\frac{1}{2}}_{\text{RF-to-IF feedthrough}} + \underbrace{\frac{2}{\pi} \cos \omega_{LO} t}_{\text{wanted frequency conversion}} + \text{o.t.} \right] \cdot V_{RF}(t)$$

50% duty cycle
 $s_{LO}(t)$ square
wave function

RF-to-IF
feedthrough

wanted
frequency conversion

at $3\omega_{LO}$
 $5\omega_{LO}$

Hyp: $V_{RF}(t) = A \cos \omega_{RF} t$

$$\Rightarrow V_{IF}(t) = \frac{R_L}{R_L + r_{on}} \cdot \left[\frac{A}{2} \cos \omega_{RF} t + \frac{1}{2} \cdot A \cdot \frac{2}{\pi} \cdot \cos(\omega_{LO} - \omega_{RF}) t + \frac{1}{2} \cdot A \cdot \frac{2}{\pi} \cos(\omega_{LO} + \omega_{RF}) t + o.t. \right]$$

RF-to-IF
wanted signal at ω_{IF}

↓

- conversion voltage gain: $A_V = \frac{V_{IF}(\omega_{LO} - \omega_{RF})}{V_{RF}(\omega_{RF})} = \frac{1}{\pi} \cdot \frac{R_L}{R_L + r_{on}}$

max. conv. gain $\rightarrow \frac{1}{\pi}$
 $\rightarrow \sim -10 \text{ dB}$

• linearity : r_{on} depends on $V_{gs} \Rightarrow$ on $V_{RF}(t)$

\Rightarrow nonlinearity

Mixer linearity \nearrow

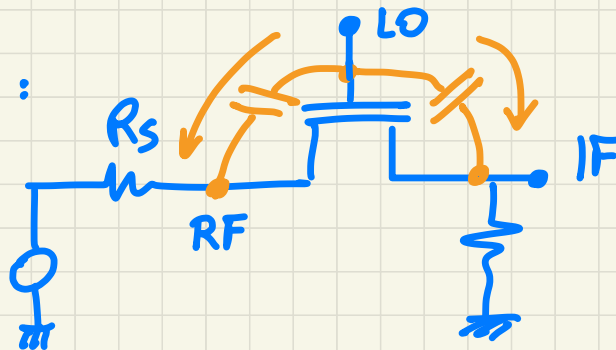
$\left\{ \begin{array}{l} \text{Tx gate} \\ r_{on} \ll R_L \end{array} \right.$



Large parasitic cap. \leftarrow

large MOSFETS

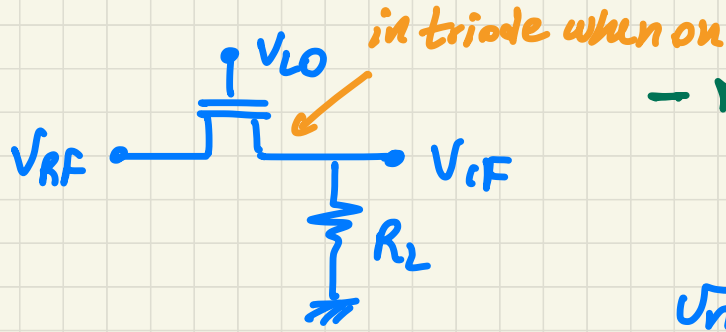
• Feedthrough :



LO-to-IF
LO-to-RF

Linearity \longleftrightarrow trade-off \longleftrightarrow Feedthrough

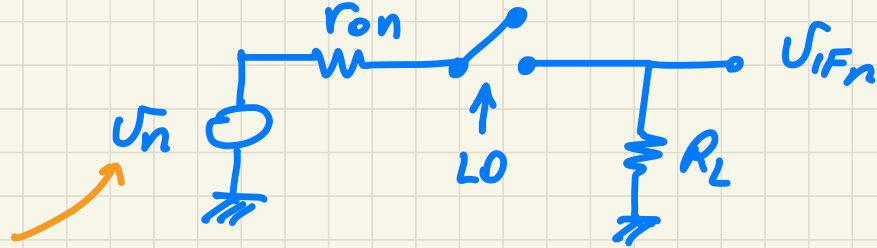
- Noise in mixers :



— MOSFET noise :

MOSFET noise

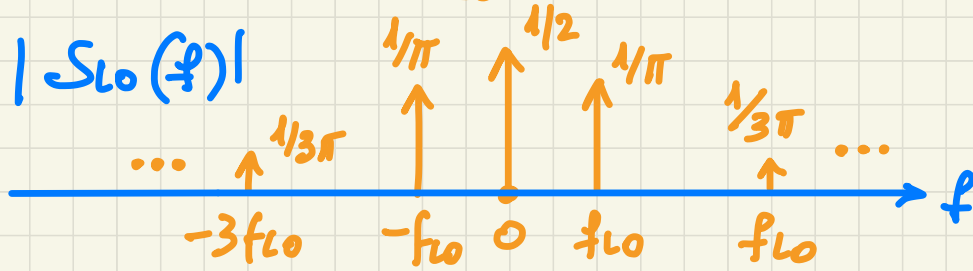
$$PSD^{SSB} = 4kT r_{on}$$



$$v_{IFn}(t) = v_n(t) \cdot s_{LO}(t) \cdot \frac{R_L}{R_L + r_{on}} \quad (LTV)$$

↓

$$PSD_{v_{IF}}^{DSB}(f) = \underbrace{PSD_n^{DSB}(f)}_{2kTr_{on}} * \underbrace{|S_{LO}(f)|^2}_{\downarrow} \cdot \left(\frac{R_L}{R_L + r_{on}} \right)^2$$

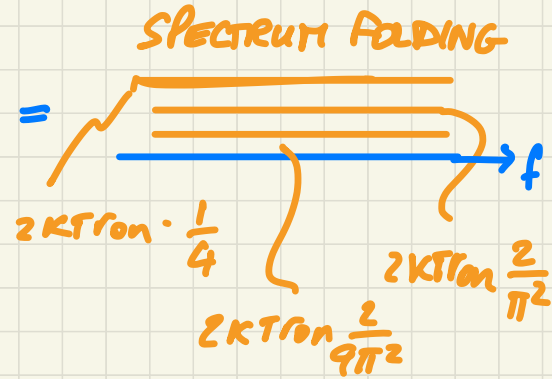
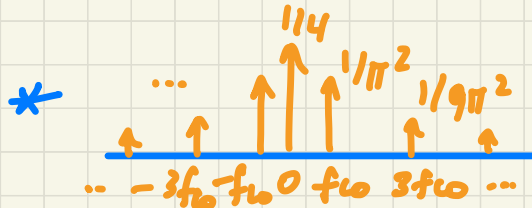
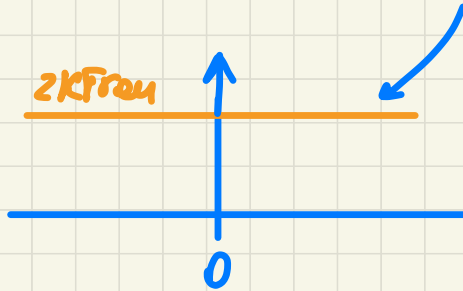


$$c_0 = 1/2$$

$$c_1 = c_{-1} = 1/\pi$$

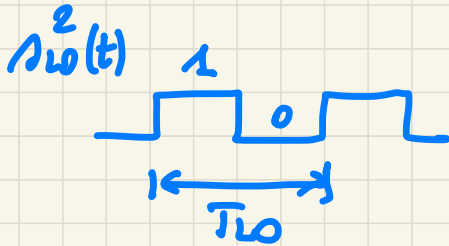
$$\vdots$$

$$\Rightarrow \text{PSD}_{\text{VIF}}^{\text{DSB}}(f) = 2kT r_{on} * \sum_{k=-\infty}^{\infty} |c_k|^2 \delta(f - kf_{LO}) \cdot \left(\frac{R_L}{R_L + r_{on}} \right)$$



$$\Rightarrow \text{PSD}_{V_{IF}}^{\text{DSB}} = 2KT r_{on} \cdot \underbrace{\sum_{k=-\infty}^{+\infty} |C_k|^2}_{\text{Power of } S_{LO}(t)} \cdot \left(\frac{R_L}{R_L + r_{on}} \right)^2$$

Parseval's theor.: $\int_{-\infty}^{+\infty} |S_{LO}(f)|^2 df = \frac{1}{T_{LO}} \int_0^{T_{LO}} |s_{LO}(t)|^2 dt$

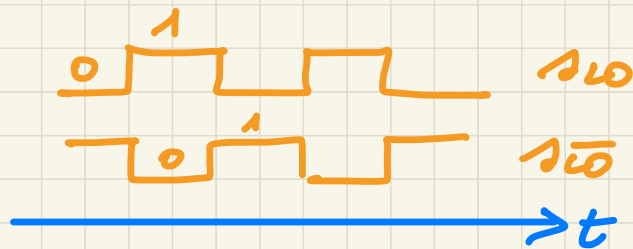
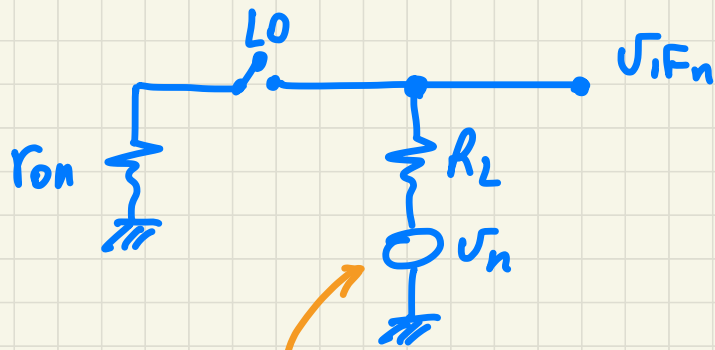


$$\sum_{k=-\infty}^{+\infty} |C_k|^2 = \frac{1}{T_{LO}} \cdot \frac{T_{LO}}{2} \cdot 1 = \frac{1}{2}$$

$$\Rightarrow \text{PSD}_{V_{IF}}^{\text{DSB}} = \cancel{2}KT r_{on} \cdot \cancel{\frac{1}{2}} \cdot \left(\frac{R_L}{R_L + r_{on}} \right)^2$$

Intuitively: V_n is transferred to V_{IF} for half of the time \Rightarrow PSD weighted by $1/2$

— R_L noise :



$$PSD^{SSB} = h k T R_L$$

$$v_{IFn}(t) = \underbrace{v_n(t) \cdot a_{LO}(t) \cdot \frac{r_{on}}{r_{on} + R_L}}_{\text{weight } 1/2} + \underbrace{v_n(t) \cdot a_{\overline{LO}}(t)}_{\text{weight } 1/2}$$

DSB $2kTR_L$

when switch is closed

when switch is open

$$PSD_{v_{IF}}^{DSB} = \cancel{2kTR_L} \cdot \frac{1}{2} \cdot \left(\frac{r_{on}}{r_{on} + R_L} \right)^2 + \cancel{2kTR_L} \cdot \frac{1}{2}$$

$$\Rightarrow \text{PSD}_{V_{IFn}}^{\text{SSB}} = 2KT r_{on} \cdot \left(\frac{R_L}{R_L + r_{on}} \right)^2 + 2KTR_L \cdot \left(\frac{r_{on}}{R_L + r_{on}} \right)^2$$

total PSD
including both
MOS and R_L noise

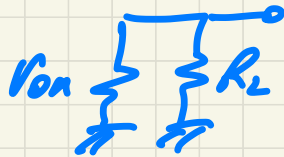
MOSFET noise

$2KTR_L$
 R_L noise

$$= 2KT \cdot (r_{on} \parallel R_L) + 2KTR_L$$

Intuitive
explanation

when switch
is closed



when switch
is open

